### N-channel 25 V 0.99 mΩ logic level MOSFET in LFPAK using NextPower technology

Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic c	haracteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 12 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15};$	-	14	-	nC
Q <sub>G(tot)</sub>	total gate charge	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 12 \text{ V}; \text{ see } \frac{\text{Figure 15}}{\text{Figure 14}};$	-	51	-	nC

<sup>[1]</sup> Continuous current is limited by package

## 2. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	D
3	S	source		$G \longrightarrow X$
4	G	gate		
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S

SOT669 (LFPAK; Power-SO8)

## 3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PSMN0R9-25YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669		

N-channel 25 V 0.99 mΩ logic level MOSFET in LFPAK using NextPower technology

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	25	V
$V_{DGR}$	drain-gate voltage	25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ		-	25	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	Α
		T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see Figure 4		-	1563	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	272	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
V <sub>ESD</sub>	electrostatic discharge voltage	MM (JEDEC JESD22-A115)		920	-	V
Source-drain	n diode					
Is	source current	T <sub>mb</sub> = 25 °C	<u>[1]</u>	-	100	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	1563	Α
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup} \le$ 25 V; unclamped; $R_{GS}$ = 50 Ω; see <u>Figure 3</u>		-	342	mJ

#### [1] Continuous current is limited by package

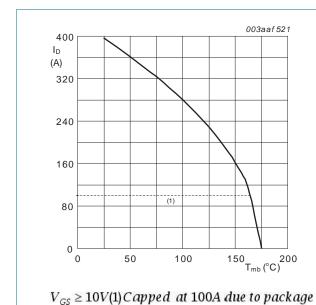


Fig 1. Continuous drain current as a function of mounting base temperature

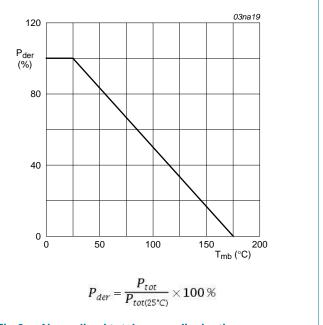
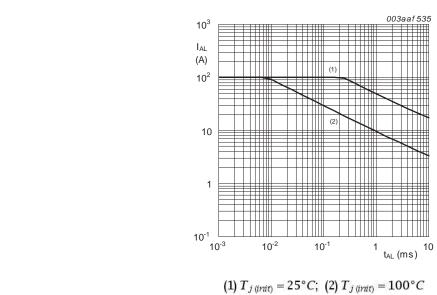


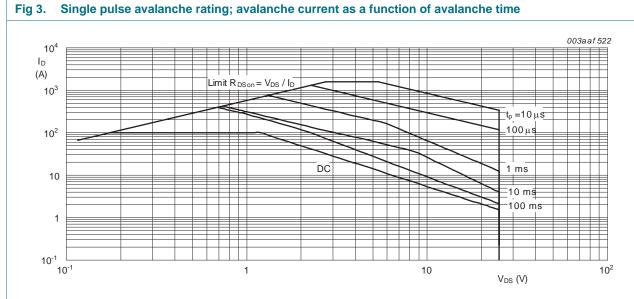
Fig 2. Normalized total power dissipation as a function of mounting base temperature

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### N-channel 25 V 0.99 m $\Omega$ logic level MOSFET in LFPAK using NextPower technology





 $T_{mb} = 25$ °C;  $I_{DM}$  is a single pulse

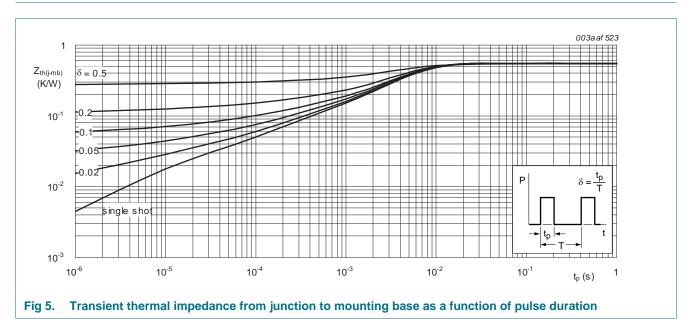
Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

N-channel 25 V 0.99 mΩ logic level MOSFET in LFPAK using NextPower technology

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	0.45	0.55	K/W



N-channel 25 V 0.99 mΩ logic level MOSFET in LFPAK using NextPower technology

## 6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics	Canditions	N#:	Ti	Mess	11:-
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	racteristics					
$V_{(BR)DSS}$	drain-source breakdown	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	25	-	-	V
	voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	22.5	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 \text{ °C}$ ; see Figure 10	1.05	1.41	1.95	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see Figure 11	-	-	2.25	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	100	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u>	-	0.95	1.25	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 150 \text{ °C};$ see Figure 12; see Figure 13	-	-	2.125	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	0.75	0.99	mΩ
		$V_{GS} = 10 \text{ V}$ ; $I_D = 25 \text{ A}$ ; $T_j = 150 \text{ °C}$ ; see Figure 12; see Figure 13	-	-	1.68	mΩ
$R_{G}$	internal gate resistance (AC)	f = 1 MHz	-	1.1	2.2	Ω
Dynamic c	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 12 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 14; see Figure 15	-	110	-	nC
		$I_D$ = 25 A; $V_{DS}$ = 12 V; $V_{GS}$ = 4.5 V; see Figure 15; see Figure 14	-	51	-	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V; see Figure 14	-	104	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	14.8	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	see Figure 14; see Figure 15	-	10.5	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	4.4	-	nC
$Q_{GD}$	gate-drain charge		-	14	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 12 V; see <u>Figure 14</u> ; see Figure 15	-	2.4	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	6775	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}$ ; see Figure 16	-	1437	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	573	-	pF

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### N-channel 25 V 0.99 mΩ logic level MOSFET in LFPAK using NextPower technology

Table 6. Characteristics ... continued

Cumbal	Dovemeter	Canditions	N#:	T	Mass	l lm!4
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$t_{d(on)}$	turn-on delay time	$V_{DS} = 12 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 4.5 \text{ V};$	-	42.5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	74	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	103.5	-	ns
t <sub>f</sub>	fall time		-	55	-	ns
Q <sub>oss</sub>	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 12 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	31.57	-	nC
Source-drain	diode					
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 17	-	8.0	1.1	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ;	-	48	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 12 \text{ V}$	-	60	-	nC
t <sub>a</sub>	reverse recovery rise time	$V_{GS} = 0 \text{ V; } I_S \text{ 25 A;}$ $dI_S/dt = -100 \text{ A/}\mu\text{s; } V_{DS} = 12 \text{ V;}$ see Figure 18	-	26.3	-	ns
t <sub>b</sub>	reverse recovery fall time	$V_{GS} = 0 \text{ V; } I_S = 25 \text{ A;}$ $dI_S/dt = -100 \text{ A/}\mu\text{s; } V_{DS} = 12 \text{ V;}$ see Figure 18	-	21.7	-	ns

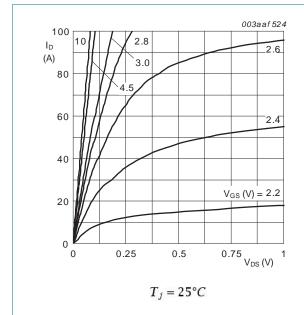
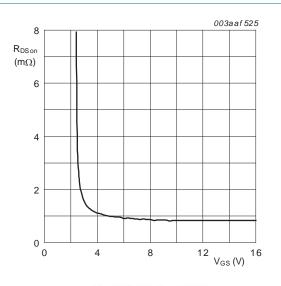


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values



 $T_j = 25^{\circ}C; I_D = 25A$ 

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### N-channel 25 V 0.99 mΩ logic level MOSFET in LFPAK using NextPower technology

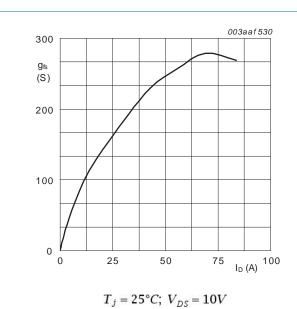
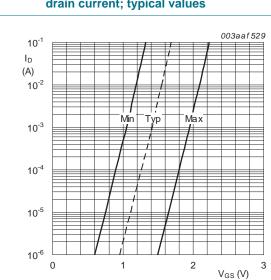
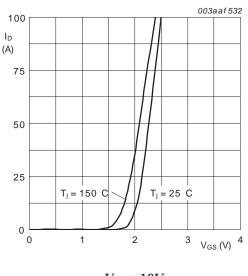


Fig 8. Forward transconductance as a function of drain current; typical values



 $T_j = 25^{\circ}C; \ V_{DS} = 5V$ 

Fig 10. Sub-threshold drain current as a function of gate-source voltage



 $V_{\rm DS}={\bf 10}V$ 

Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

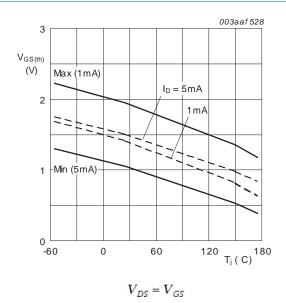


Fig 11. Gate-source threshold voltage as a function of junction temperature

### N-channel 25 V 0.99 mΩ logic level MOSFET in LFPAK using NextPower technology

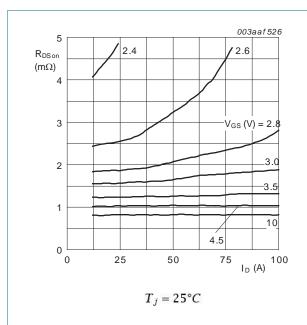


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

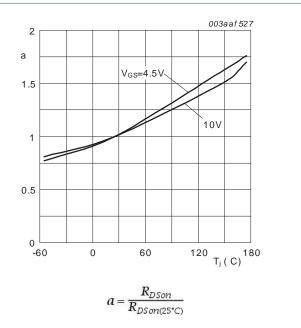


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

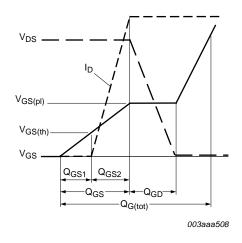
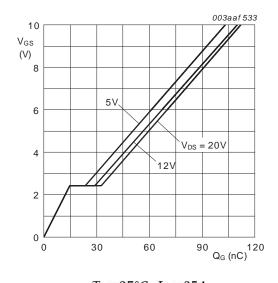


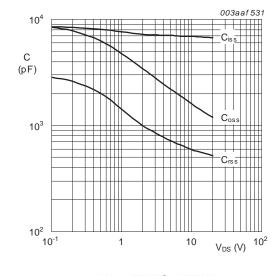
Fig 14. Gate charge waveform definitions



 $T_j = 25^{\circ}C; \ I_D = 25A$ 

Fig 15. Gate-source voltage as a function of gate charge; typical values

### N-channel 25 V 0.99 m $\Omega$ logic level MOSFET in LFPAK using NextPower technology



 $V_{GS} = 0V; f = 1MHz$ 

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

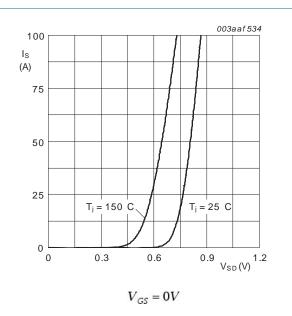


Fig 17. Source current as a function of source-drain voltage; typical values

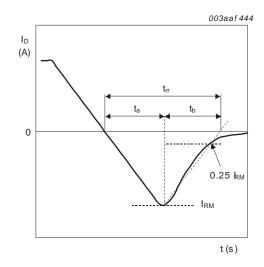


Fig 18. Reverse recovery timing definition

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## 7. Package outline

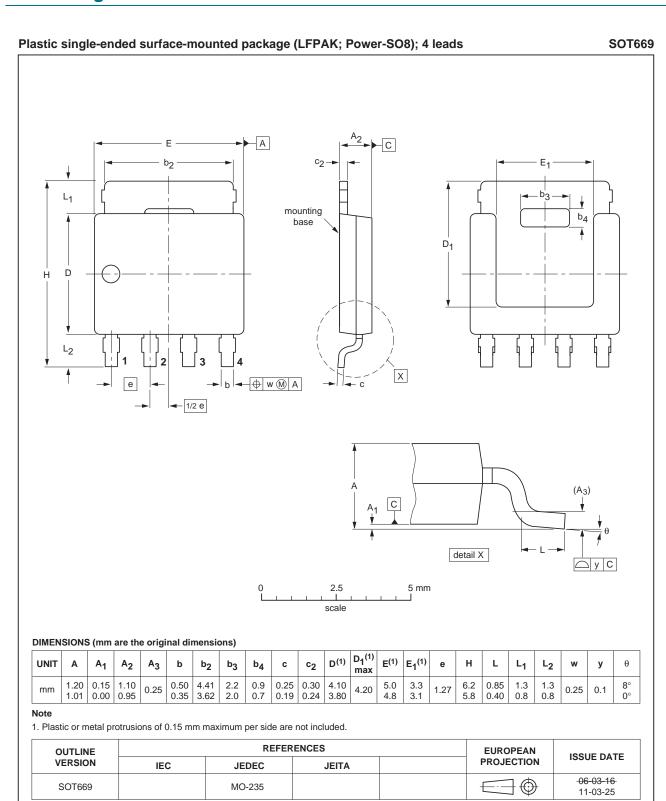


Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

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## 8. Revision history

#### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN0R9-25YLC v.2	20110704	Product data sheet	-	PSMN0R9-25YLC v.1
Modifications:	<ul> <li>Various changes to</li> </ul>	content.		
PSMN0R9-25YLC v.1	20101202	Product data sheet	-	-

#### N-channel 25 V 0.99 mΩ logic level MOSFET in LFPAK using NextPower technology

### 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# PSMN0R9-25YLC

N-channel 25 V 0.99 m $\Omega$  logic level MOSFET in LFPAK using NextPower technology

### 11. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
1.4	Quick reference data
2	Pinning information
3	Ordering information
4	Limiting values
5	Thermal characteristics
6	Characteristics
7	Package outline
8	Revision history12
9	Legal information13
9.1	Data sheet status
9.2	Definitions13
9.3	Disclaimers
9.4	Trademarks14
10	Contact information14

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Date of release: 04 July 2011